```
=> file reg
FILE 'REGISTRY' ENTERED AT 14:05:25 ON 28 JUL 2005
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=> d his

     FILE 'LREGISTRY' ENTERED AT 13:36:36 ON 28 JUL 2005
L1              STR

     FILE 'REGISTRY' ENTERED AT 13:47:01 ON 28 JUL 2005
L2              SCR 2043
L3            0 S L1 AND L2
L4            0 S L1 AND L2 FUL

     FILE 'HCAPLUS' ENTERED AT 14:03:22 ON 28 JUL 2005
L5          238 S YUEH ?/AU
L6           32 S PUTNA ?/AU
L7            1 S L5 AND L6

     FILE 'REGISTRY' ENTERED AT 14:05:25 ON 28 JUL 2005


=> d 14 que stat
L1              STR
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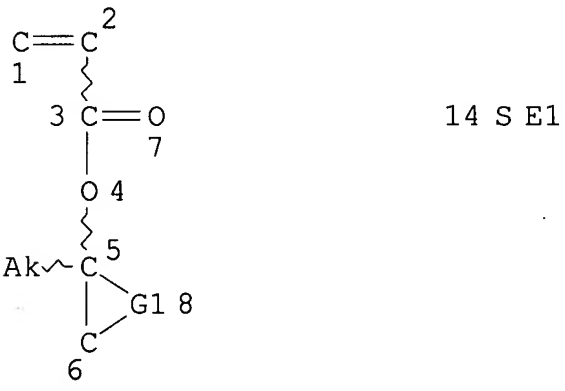

14 S E1

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REP G1=(1-5) C
NODE ATTRIBUTES:
HCOUNT  IS E1     AT  14
CONNECT IS E1  RC AT   9
CONNECT IS X1  RC AT  14
DEFAULT MLEVEL IS ATOM
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GGCAT IS SAT AT 9
DEFAULT ECLEVEL IS LIMITED

GRAPH ATTRIBUTES:
RING(S) ARE ISOLATED OR EMBEDDED
NUMBER OF NODES IS 10

STEREO ATTRIBUTES: NONE
L2 SCR 2043
L4 0 SEA FILE=REGISTRY SSS FUL L1 AND L2

100.0% PROCESSED 1347 ITERATIONS 0 ANSWERS
SEARCH TIME: 00.00.01

=> file hcaplus
FILE 'HCAPLUS' ENTERED AT 14:05:34 ON 28 JUL 2005
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=> d l7 1 all

authors' citation

L7 ANSWER 1 OF 1 HCAPLUS COPYRIGHT 2005 ACS on STN
AN 2005:638587 HCAPLUS
ED Entered STN: 22 Jul 2005
TI Reducing outgassing of reactive material upon exposure of photolithography resists
IN **Yueh, Wang; Putna, Ernisse S.**
PA USA
SO U.S. Pat. Appl. Publ., 4 pp.
CODEN: USXXCO
DT Patent
LA English
IC ICM G03C001-492
INCL 430270100
CC 74 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI US 2005158654	A1	20050721	US 2004-761842	200401 21

PRAI US 2004-761842 20040121

CLASS

PATENT NO.	CLASS	PATENT FAMILY CLASSIFICATION CODES
US 20050158654	ICM	G03C001-492
	INCL	430270100
US 2005158654	NCL	430/270.100

AB Outgassing of reactive material upon exposure of a photolithographic resist may be reduced. Outgassing may foul optical components of the photolithographic system. In one embodiment, a ring compound with iodine or sulfur may be formed. The ring compound may be more resistant to the generation of reactive outgassing components.